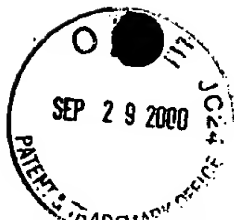


MICRON.009DV1



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#17/D
JRM

Applicant : Schuegraf et al.) Group Art Unit 2811
Appl. No. : 08/932,228)
Filed : September 17, 1997)
For : SHALLOW TRENCH)
ISOLATION USING LOW)
DIELECTRIC CONSTANT)
INSULATOR)
Examiner : H. VU)

PRELIMINARY AMENDMENT

RECEIVED
OCT 4 2000
TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits in the present continued prosecution application (CPA), please amend the above-captioned application as indicated below.

IN THE CLAIMS:

11. (Twice Amended) An isolation structure in a semiconductor substrate comprising:
- a recessed portion formed [therein in] with a vertical sidewall within the semiconductor substrate; and
- a dielectric material comprising a halide-doped silicon oxide filling the recessed portion, said dielectric material having a dielectric constant lower than the dielectric constant of silicon dioxide.

Please add the following new claims: